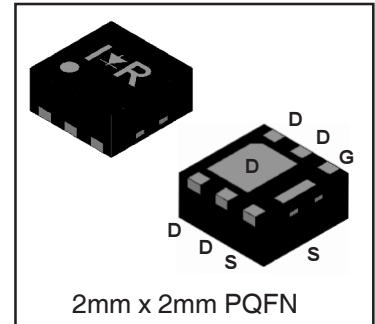
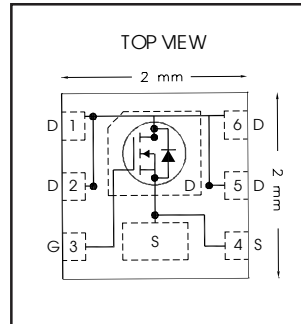


IRFHS8242PbF

HEXFET® Power MOSFET

V_{DS}	25	V
$V_{GS\ max}$	±20	V
$R_{DS(on)\ max}$ (@ $V_{GS} = 10V$)	13.0	mΩ
Q_g (typical) (@ $V_{GS} = 4.5V$)	4.3	nC
I_D (@ $T_{c(Bottom)} = 25°C$)	8.5 ②	A



Applications

- System/Load Switch

Features and Benefits

Features

Low R_{DSon} ($\leq 13.0m\Omega$)
Low Thermal Resistance to PCB ($\leq 13°C/W$)
Low Profile ($\leq 1.0\ mm$)
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Consumer Qualification

results in

Resulting Benefits

Lower Conduction Losses
Enable better thermal dissipation
Increased Power Density
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFHS8242TRPBF	PQFN 2mm x 2mm	Tape and Reel	4000	
IRFHS8242TR2PBF	PQFN 2mm x 2mm	Tape and Reel	400	

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	25	V
V_{GS}	Gate-to-Source Voltage	±20	
$I_D @ T_A = 25°C$	Continuous Drain Current, $V_{GS} @ 10V$	9.9②	A
$I_D @ T_A = 70°C$	Continuous Drain Current, $V_{GS} @ 10V$	8.0	
$I_D @ T_{c(Bottom)} = 25°C$	Continuous Drain Current, $V_{GS} @ 10V$	21③	
$I_D @ T_{c(Bottom)} = 70°C$	Continuous Drain Current, $V_{GS} @ 10V$	17③	
$I_D @ T_{c(Bottom)} = 25°C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited)	8.5②	
I_{DM}	Pulsed Drain Current ①	84	
$P_D @ T_A = 25°C$	Power Dissipation ④	2.1	W
$P_D @ T_A = 70°C$	Power Dissipation ④	1.3	
	Linear Derating Factor ④	0.02	W/°C
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

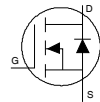
Notes ① through ⑥ are on page 2

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	25	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	18	—	mV/°C	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	10.0	13.0	mΩ	$V_{GS} = 10V, I_D = 8.5A$ ②
		—	17.0	21.0		$V_{GS} = 4.5V, I_D = 6.8A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.8	2.35	V	$V_{DS} = V_{GS}, I_D = 25\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-6.8	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	19	—	—	S	$V_{DS} = 10V, I_D = 8.5A$ ②
Q_g	Total Gate Charge ⑥	—	4.3	—	nC	$V_{GS} = 4.5V, V_{DS} = 13V, I_D = 8.5A$ ②
Q_g	Total Gate Charge ⑥	—	10.4	—	nC	$V_{DS} = 13V$
Q_{gs}	Gate-to-Source Charge ⑥	—	1.8	—		$V_{GS} = 10V$
Q_{gd}	Gate-to-Drain Charge ⑥	—	1.6	—		$I_D = 8.5A$ ② (See Fig. 6 & 16)
R_G	Gate Resistance	—	1.9	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	6.5	—	ns	$V_{DD} = 13V, V_{GS} = 4.5V$ ③
t_r	Rise Time	—	19	—		$I_D = 8.5A$ ②
$t_{d(off)}$	Turn-Off Delay Time	—	5.4	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	5.3	—		See Fig.17
C_{iss}	Input Capacitance	—	653	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	171	—		$V_{DS} = 10V$
C_{riss}	Reverse Transfer Capacitance	—	78	—		$f = 1.0MHz$

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	8.5 ②	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	84		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 8.5A$ ②, $V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	11	17	ns	$T_J = 25^\circ\text{C}, I_F = 8.5A$ ②, $V_{DD} = 13V$
Q_{rr}	Reverse Recovery Charge	—	11	17	nC	$di/dt = 280 A/\mu s$ ③
t_{on}	Forward Turn-On Time	Time is dominated by parasitic Inductance				



Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case ⑤	—	13	°C/W
$R_{\theta JC}$ (Top)	Junction-to-Case ⑤	—	90	
$R_{\theta JA}$	Junction-to-Ambient ④	—	60	
$R_{\theta JA}$	Junction-to-Ambient (<10s) ④	—	42	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Current limited by package.
- ③ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board
- ⑤ R_{θ} is measured at T_J of approximately 90°C .
- ⑥ For DESIGN AID ONLY, not subject to production testing.

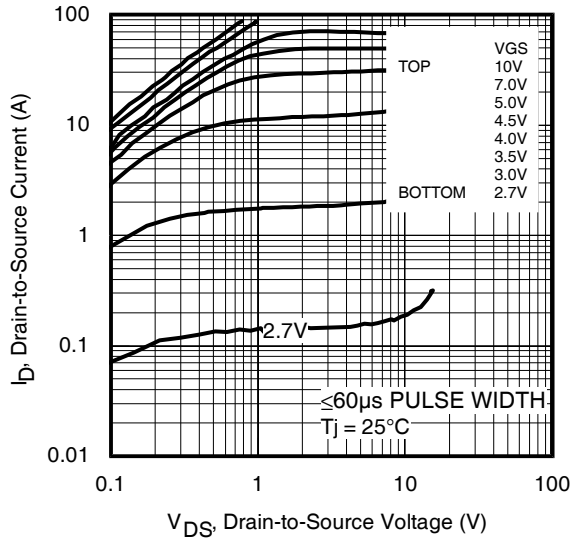


Fig 1. Typical Output Characteristics

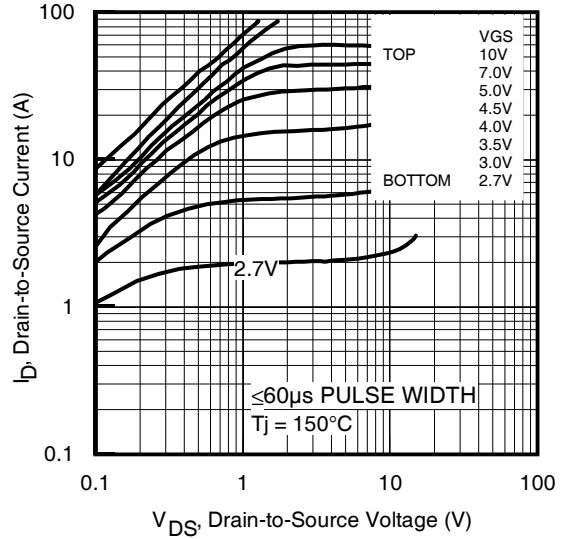


Fig 2. Typical Output Characteristics

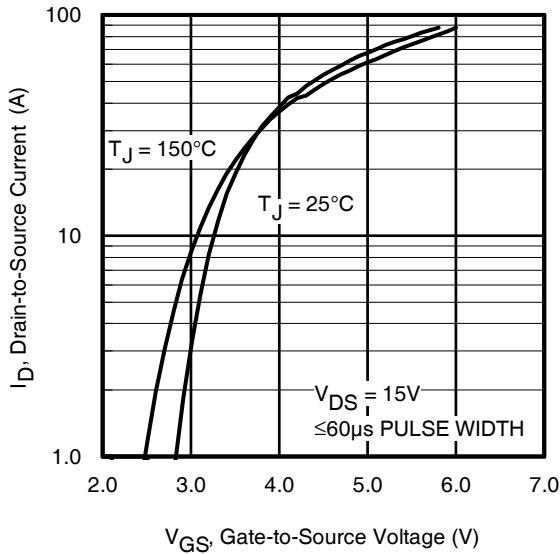


Fig 3. Typical Transfer Characteristics

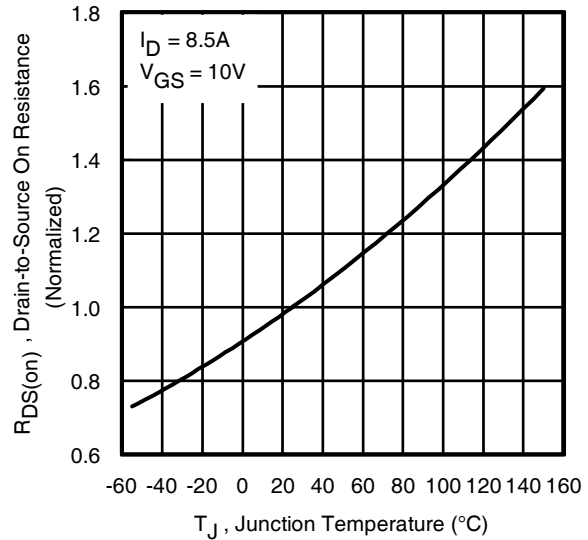


Fig 4. Normalized On-Resistance vs. Temperature

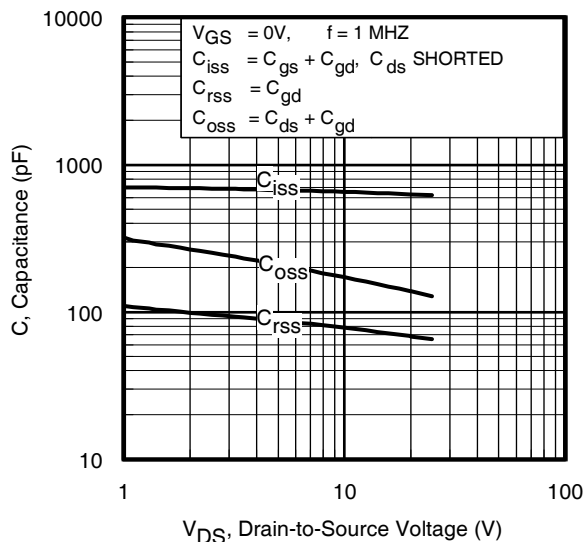


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage
www.irf.com

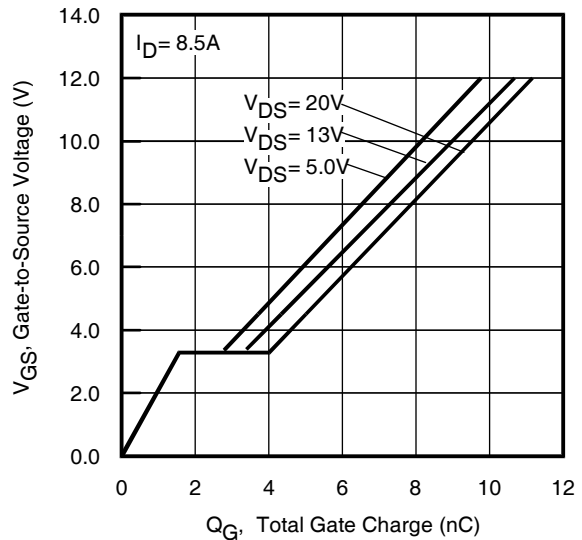


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

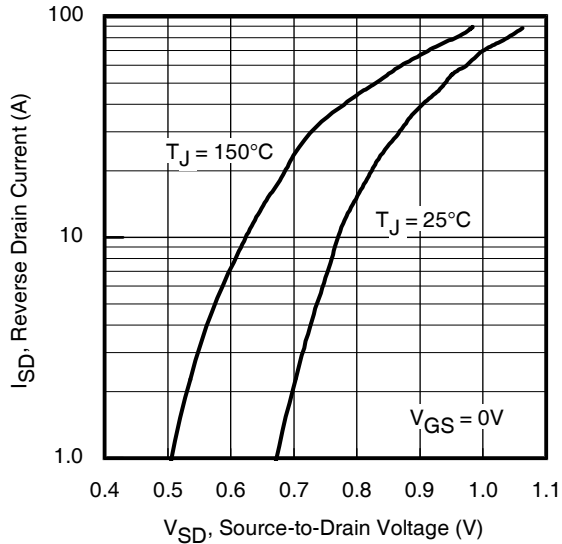


Fig 7. Typical Source-Drain Diode Forward Voltage

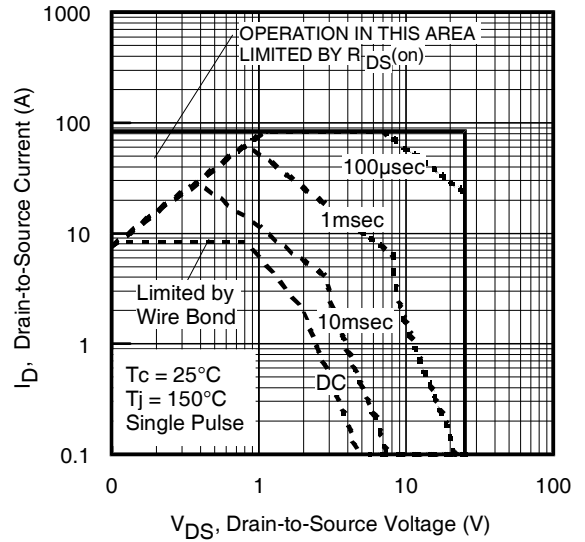


Fig 8. Maximum Safe Operating Area

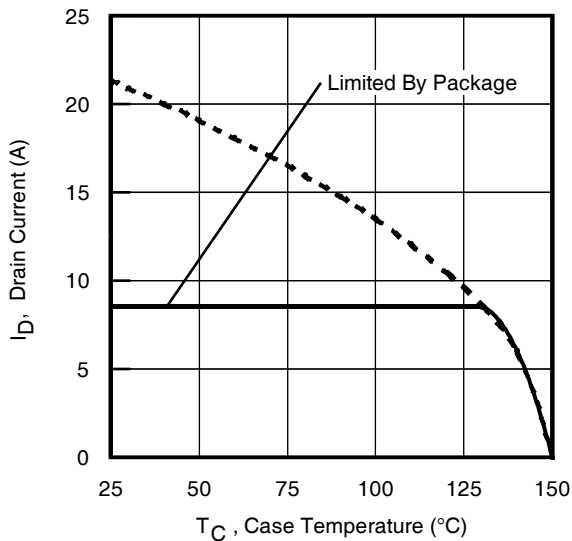


Fig 9. Maximum Drain Current vs. Case (Bottom) Temperature

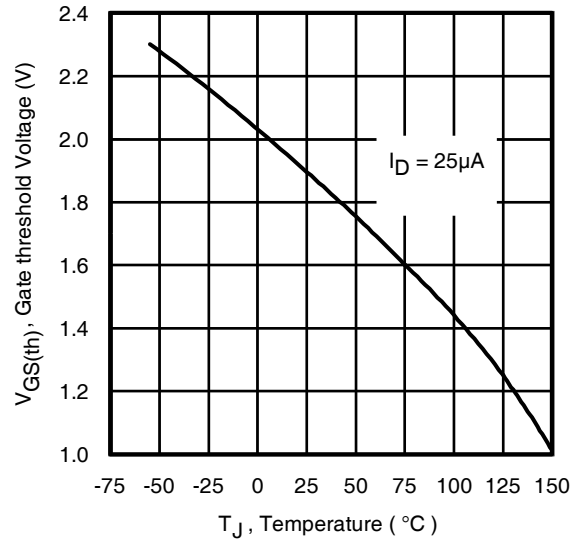


Fig 10. Threshold Voltage vs. Temperature

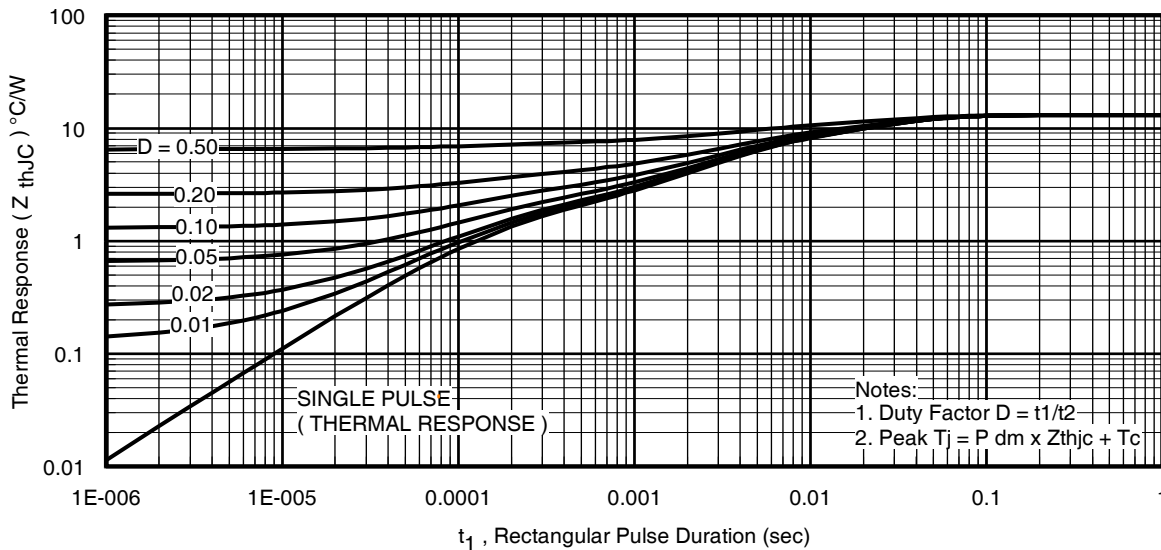


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case (Bottom)

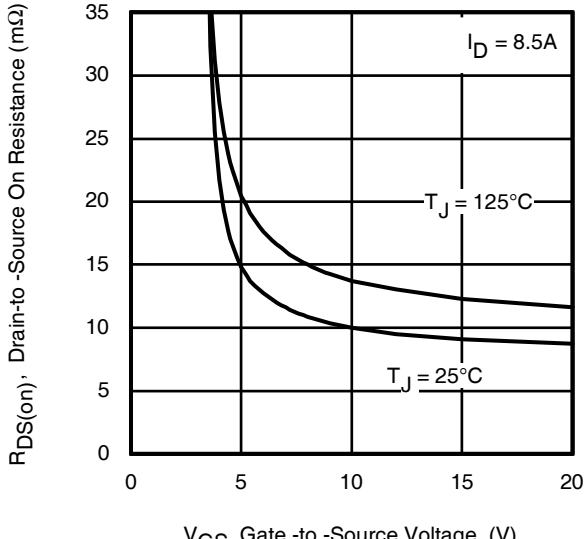


Fig 12. On-Resistance vs. Gate Voltage

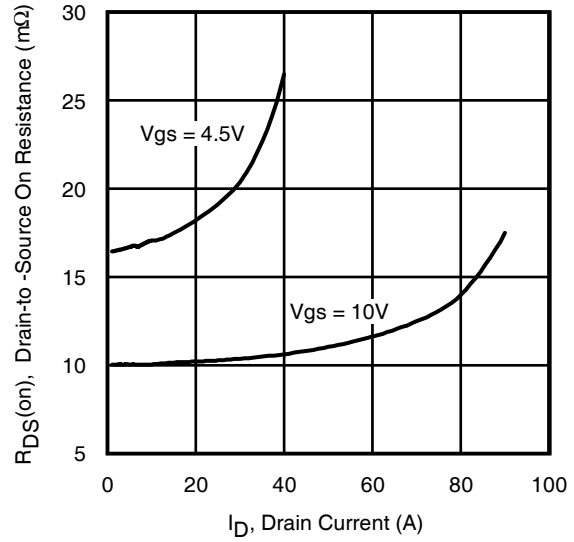


Fig 13. Typical On-Resistance vs. Drain Current

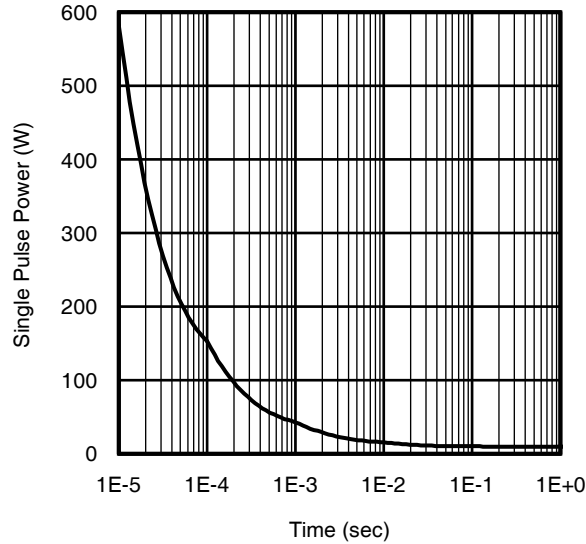
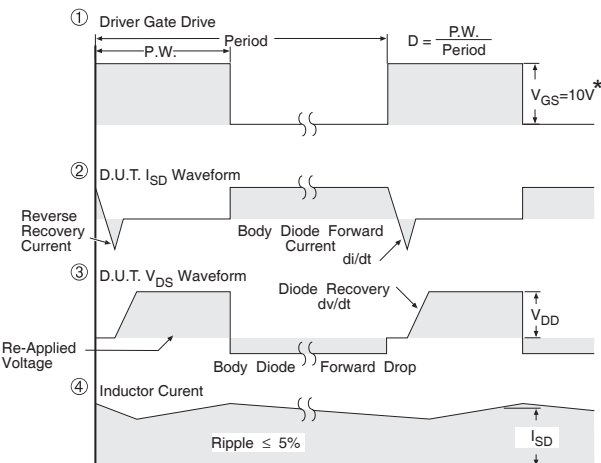
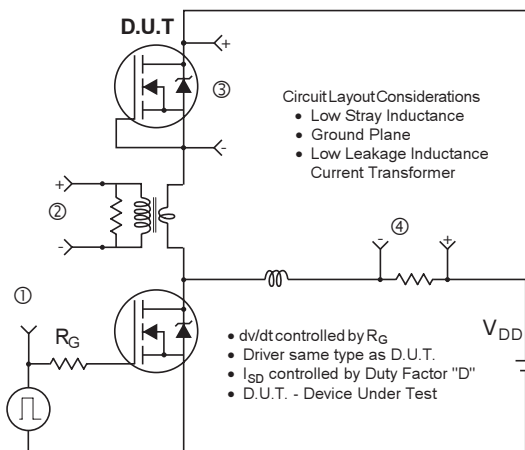


Fig 14. Typical Power vs. Time



* $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET[®] Power MOSFETs

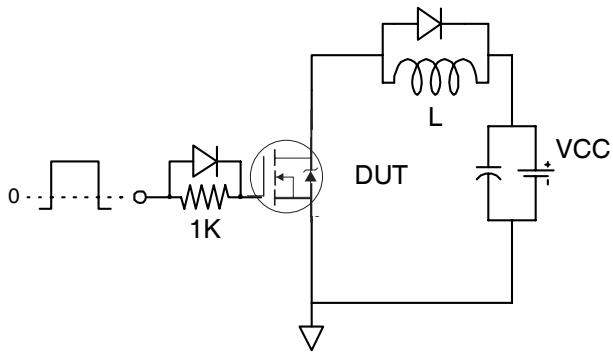


Fig 16a. Gate Charge Test Circuit

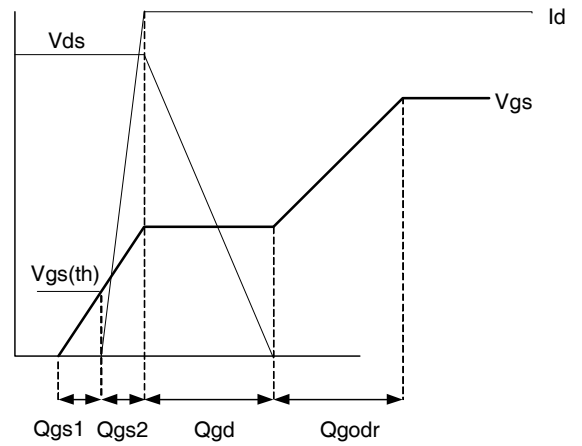


Fig 16b. Gate Charge Waveform

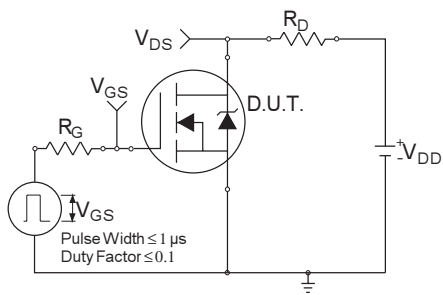


Fig 17a. Switching Time Test Circuit

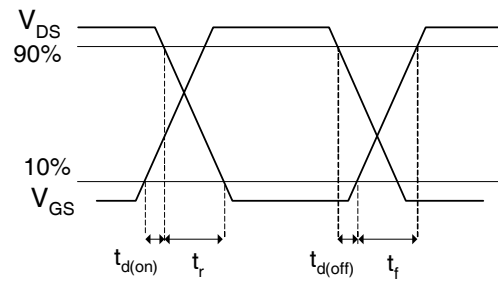
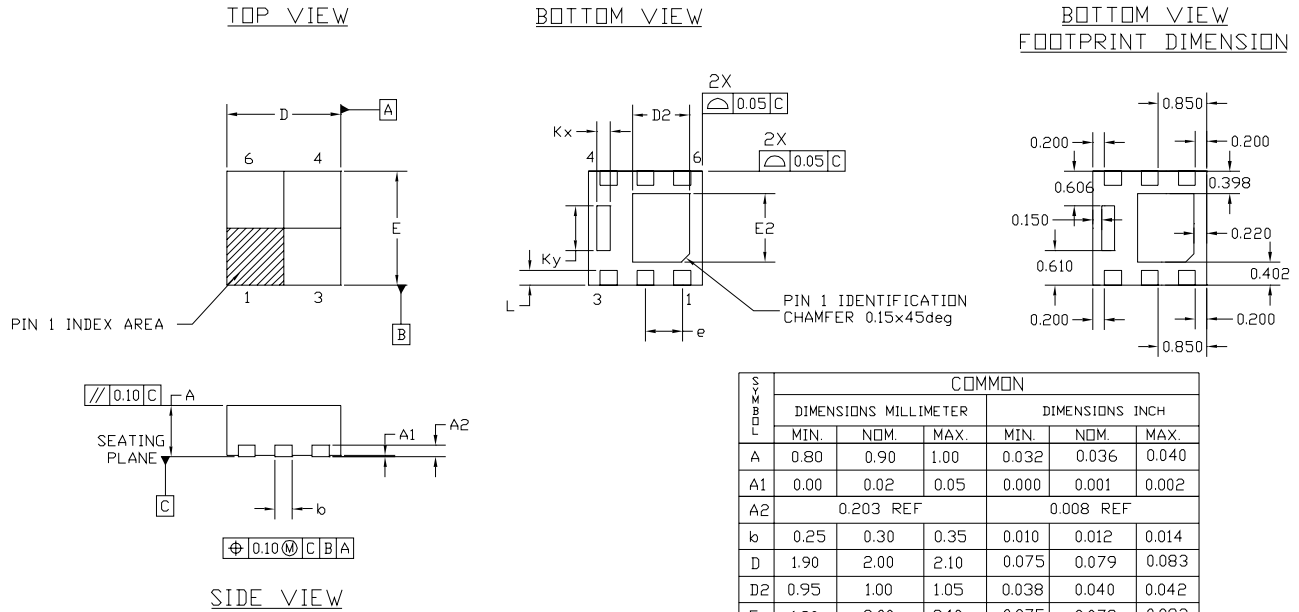


Fig 17b. Switching Time Waveforms

PQFN 2x2 Outline Package Details

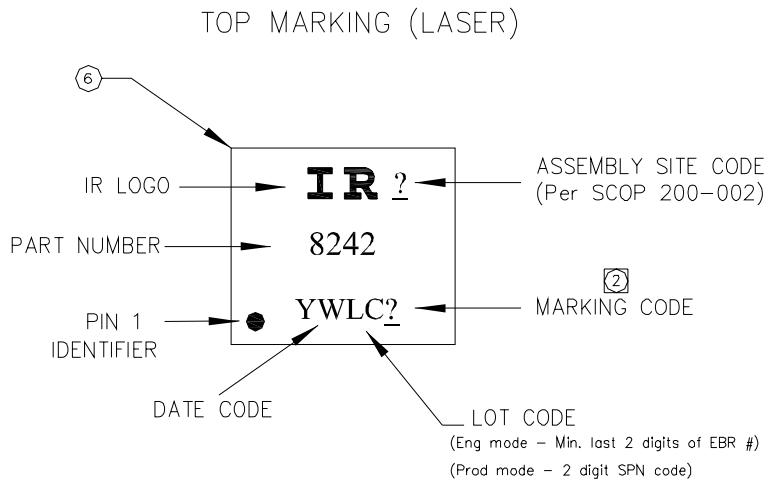


NOTES :

1. DIMENSION AND TOLERANCING CONFORM TO ASME Y14.5M-1994.
2. CONTROLLING DIMENSIONS : MILLIMETER
3. DIMENSION b APPLIES TO METALLIZED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm. FROM TERMINAL TIP.

For footprint and stencil design recommendations, please refer to application note AN-1154 at <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

PQFN 2x2 Outline Part Marking



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

PQFN 2x2 Outline Tape and Reel

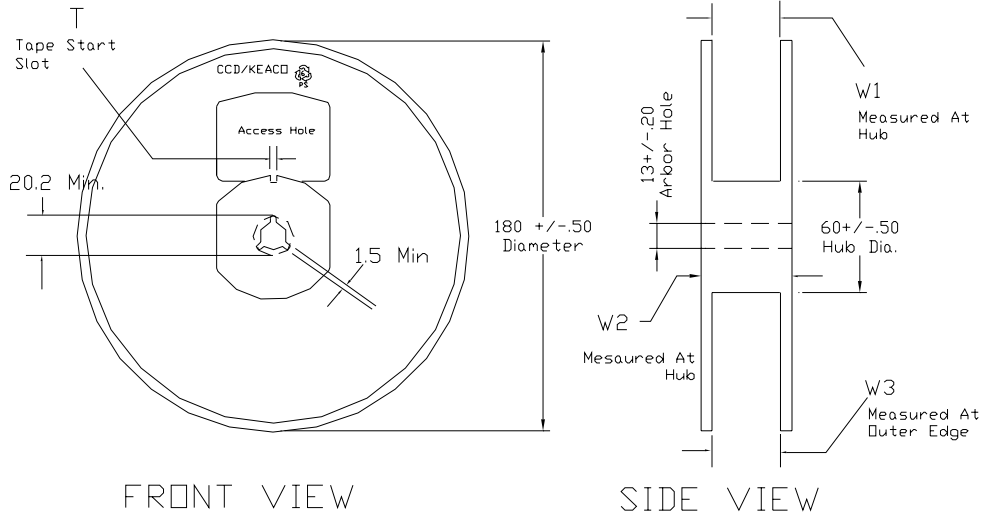
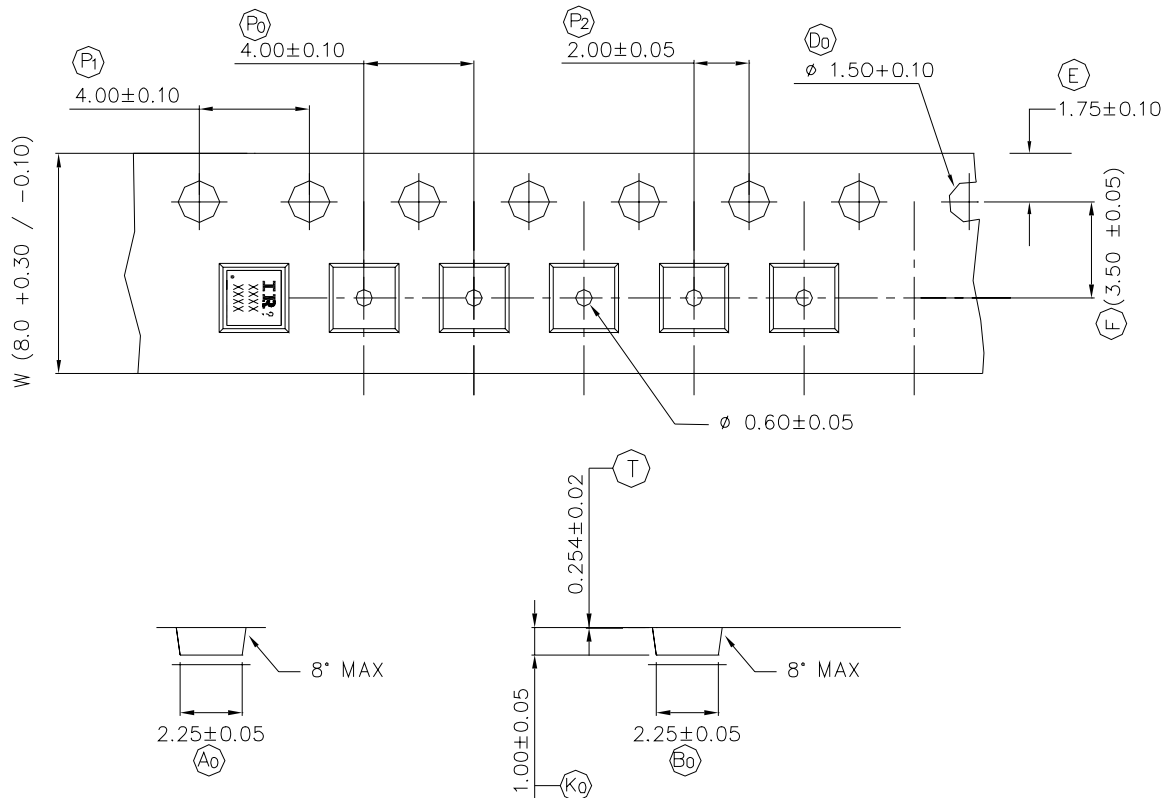


TABLE 1: REEL DETAILS

TAPE WIDTH	T	W1	W2	W3	PART NO
8 MM	3 ± 0.50	8.4 ^{+1.5} _{-0.0}	14.4 Max	7.90 Min 10.9 Max	91586-1
12 MM	5 ± 0.50	12.4 ^{+2.0} _{-0.0}	18.4 Max	11.9 Min 15.4 Max	91586-2

Note: Surface resistivity is $\geq 1 \times 10^5$ but $< 1 \times 10^{12}$ ohm/sq.



Qualification information[†]

Qualification level	Consumer ^{††} (per JEDEC JESD47F ^{†††} guidelines)	
Moisture Sensitivity Level	PQFN 2mm x 2mm	MSL 1 (per JEDEC J-STD-020D ^{†††})
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site
<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.
 Please contact your International Rectifier sales representative for further information:
<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

Data and specifications subject to change without notice.

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